

Silicon NPN Darlington Power Transistor

BDX63/A/B/C

DESCRIPTION

- Collector Current $-I_C = 8A$
- High DC Current Gain $-h_{FE} = 1000(\text{Min}) @ I_C = 3A$
- Complement to Type BDX62/A/B/C

APPLICATIONS

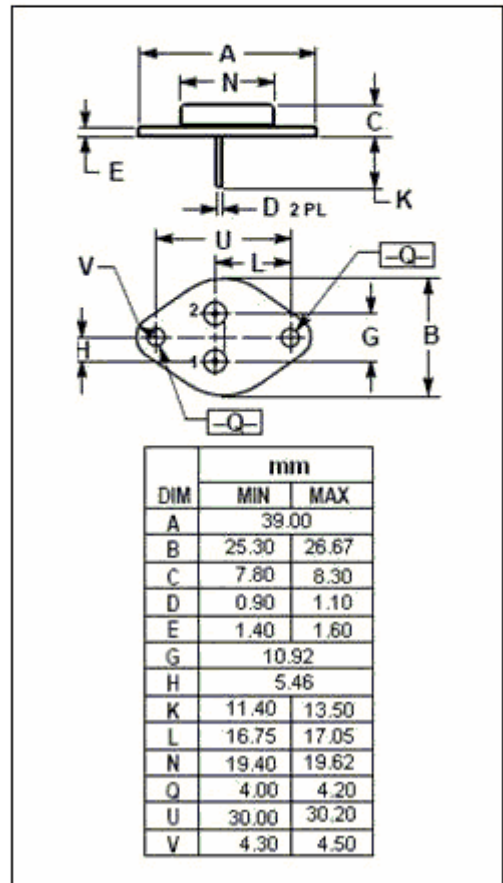
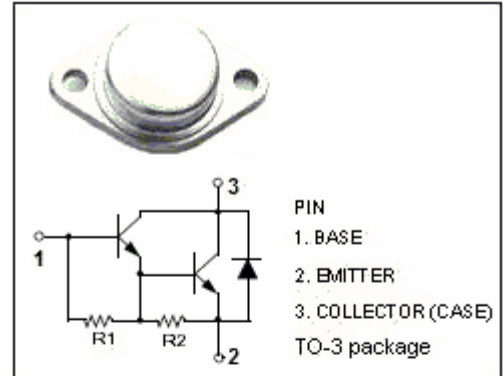
- Designed for audio output stages and general amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS($T_a=25$)

SYMBOL	PARAMETER	VALUE	UNIT	
V_{CBO}	Collector-Base Voltage	BDX63	80	V
		BDX63A	100	
		BDX63B	120	
		BDX63C	140	
V_{CEO}	Collector-Emitter Voltage	BDX63	60	V
		BDX63A	80	
		BDX63B	100	
		BDX63C	120	
V_{EBO}	Emitter-Base Voltage	5	V	
I_C	Collector Current-Continuous	8	A	
I_{CM}	Collector Current-Peak	12	A	
I_B	Base Current-Continuous	0.15	A	
P_C	Collector Power Dissipation @ $T_C=25$	90	W	
T_J	Junction Temperature	200		
T_{stg}	Storage Temperature Range	-65~200		

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1.94	/W



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ELECTRICAL CHARACTERISTICS

 $T_C=25$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
$V_{CE(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=100mA; I_B=0$	BDX63	60			V
			BDX63A	80			
			BDX63B	100			
			BDX63C	120			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=3A; I_B=12mA$			2	V	
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=3A; V_{CE}=3V$			2.5	V	
V_{ECF}	C-E Diode Forward Voltage	$I_F=3A$		1.2		V	
I_{CEO}	Collector Cutoff Current	$V_{CE}=1/2V_{CE0max}; I_B=0$			0.2	mA	
I_{CBO}	Collector Cutoff Current	$V_{CB}=V_{CE0max}; I_E=0$ $V_{CB}=1/2V_{CB0max}; I_E=0; T_J=200$			0.2 2	mA	
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5V; I_C=0$			5	mA	
h_{FE-1}	DC Current Gain	$I_C=0.5A; V_{CE}=3V$		2500			
h_{FE-2}	DC Current Gain	$I_C=3A; V_{CE}=3V$	1000				
h_{FE-3}	DC Current Gain	$I_C=8A; V_{CE}=3V$		2600			
C_{OB}	Output Capacitance	$I_E=0; V_{CB}=10V; f_{test}=1MHz$		100		pF	

Switching times

t_{on}	Turn-on Time	$I_C=3A; I_{B1}=-I_{B2}=12mA$		0.5		μs
t_{off}	Turn-off Time			5		μs